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IN THE CLAIMS

Please amend the claims as follows:

1. (original) A silicon annealed wafer, on the surface of which a COP defect free layer having a thickness of 5 μm or more is formed by annealing a base material wafer, wherein said base material wafer includes:

a COP defect region of a single crystal containing nitrogen at a concentration of less than $1 \times 10^{14}$ atoms/cm$^3$, wherein said COP defect has a size of 0.1 μm or less in the highest frequency of occurrence and there exist no COP defects having a size of more than 0.2 μm;

oxygen precipitates formed at a density of $1 \times 10^4$ counts /cm$^2$ or more when said base material wafer is subjected to a oxygen precipitate evaluation heat treatment; wherein

the ratio of the maximum to the minimum of BMD (oxygen precipitate) density is 3 or less in the radial direction of said base material wafer.

2. (original) A silicon annealed wafer according to Claim 1, wherein the oxygen concentration of said base material wafer is $11 \times 10^{17} - 17 \times 10^{17}$ atoms/cm$^3$ (ASTM F-121, 1979).

3. (original) A silicon annealed wafer according to Claim 1, wherein said COP defect occurrence region extends over an 80% or more surface area of said base material wafer in the radial direction.

4. (previously presented) A silicon annealed wafer according to Claim 1, wherein the annealing process is performed at 1100°C – 1250°C for 1 – 4 hours in a hydrogen gas, argon gas, helium gas or a mixed gas thereof.

5-7. canceled

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8. (previously presented) A silicon epitaxial wafer produced by forming an epitaxial layer on the surface of a base material wafer,

wherein said base material wafer includes:

a COP defect occurrence region of a single crystal containing nitrogen at a concentration of less than $1 \times 10^{14}$ atoms/cm$^3$, wherein said COP defect has a size of 0.1 μm or less in the highest frequency of occurrence and there exist no COP defects having a size of more than 0.2 μm;

oxygen precipitates formed at a density of $1 \times 10^4$ counts /cm$^2$ by applying an oxygen precipitate evaluation heat treatment; wherein

the ratio of the maximum to the minimum of BMD (oxygen precipitate) density is 3 or less in the radial direction of said base material wafer.

9. (original) A silicon epitaxial wafer according to Claim 8, wherein the oxygen concentration of said base material wafer is $11 \times 10^{17} - 17 \times 10^{17}$ atoms/cm$^3$ (ASTM F-121, 1979).

10. (original) A silicon epitaxial wafer according to Claim 8, wherein said COP defect occurrence region extends over an 80% or more surface area of said base material wafer in the radial direction.

11-15. canceled.